

INTRODUCE:

HVGT Half Bridge high voltage silicon rectifier assembly is made of high quality silicon GPP chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High reliability design.
2. High voltage design.
3. Power frequency ratio.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. High voltage generator.
2. Industrial microwave power supply.
3. High voltage rectifier used in electrostatic cleaning.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: screw holes M6.
3. Net weight: 2100 grams (approx).

SHAPE DISPLAY:

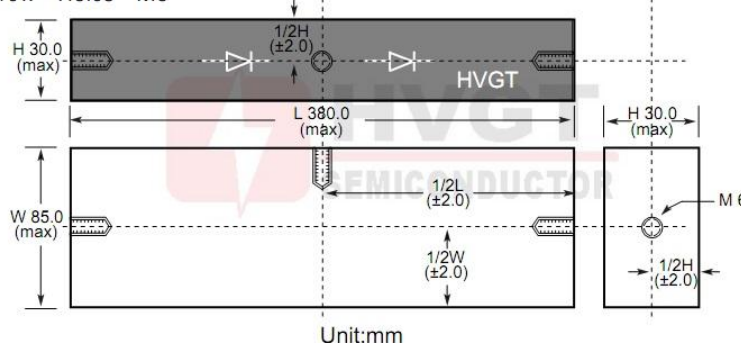


SIZE: (Unit:mm)

HVGT NAME: HVD-380

HVD-380 Series

Screw Holes M6

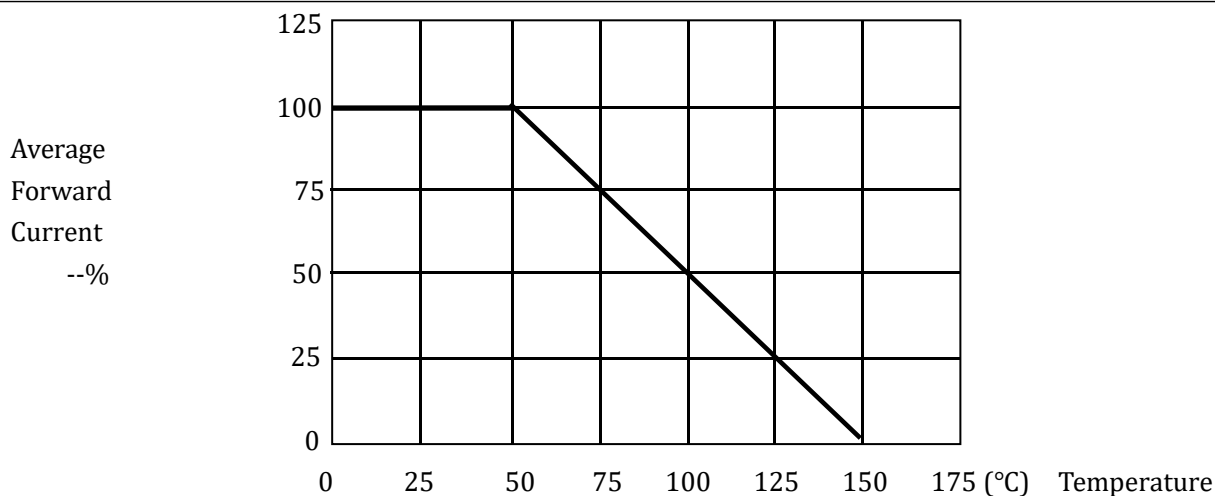
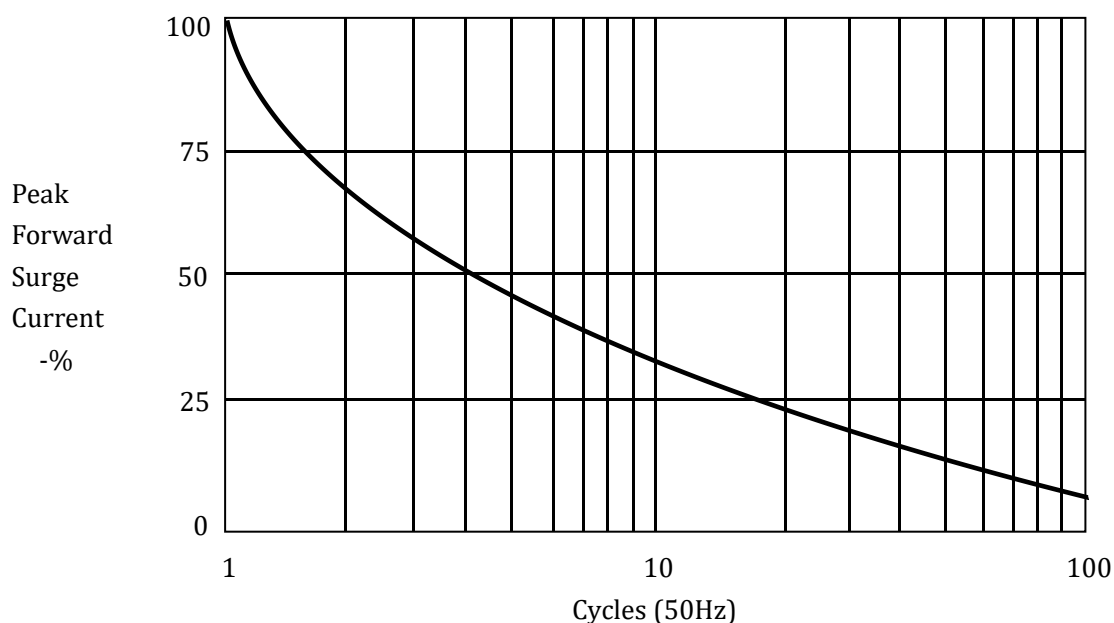


MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value		Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^{\circ}C$; $I_R=1.0\mu A$	200	200	kV
Peak Working Reverse Voltage	V_{RWM}	$T_A=25^{\circ}C$; $I_R=1.0\mu A$	200	200	kV
Non-Repetitive Peak Reverse Voltage	V_{RSM}	$T_A=25^{\circ}C$; $I_R=1.0\mu A$	240	240	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=50^{\circ}C$; 50Hz Half-sine Wave; Resistance load	2.0		A
Non-Repetitive Forward Surge Current	I_{FSM}	$T_A=25^{\circ}C$; 50Hz Half-Sine Wave; 8.3ms	60		A
Junction Temperature	T_J		150		$^{\circ}C$
Allowable Operation Case Temperature	T_C		-40~+150		$^{\circ}C$
Storage Temperature	T_{STG}		-40~+150		$^{\circ}C$

ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value		Units
Maximum Forward Voltage Drop	V_{FM}	at $25^{\circ}C$; at I_{FAVM}	220	220	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	5.0		μA
	I_{R2}	at $100^{\circ}C$; at V_{RRM}	50		μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	--		nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	--		pF

Forward Current Derating Curve

Non-Repetitive Surge Current

MARKING:

Marking	Type	Code	Cathode Mark
	HBG020D201D	HBG020D201D HVGT	

PART NUMBER NOTE:

Type	Chip	I _{F(AV)}	Frequency	V _{RRM}	T _{RR}
HB	G	020	D	201	D
Half Bridge Series	GPP Chip	2.0A	D=Doubler. P=Positive Center Tap. N=Negative Center Cap.	200kV	(U)75ns (G)100ns (D) Standard Recovery Time